



SPN7002T

Dual N-Channel Enhancement Mode MOSFET

DESCRIPTION

The SPN7002T is the Dual N-Channel enhancement mode field effect transistors are produced using high cell density DMOS technology. These products have been designed to minimize on-state resistance while provide rugged, reliable, and fast switching performance. They can be used in most applications requiring up to 640mA DC and can deliver pulsed currents up to 950mA. These products are particularly suited for low voltage, low current applications such as small servo motor control, power MOSFET gate drivers, and other switching applications.

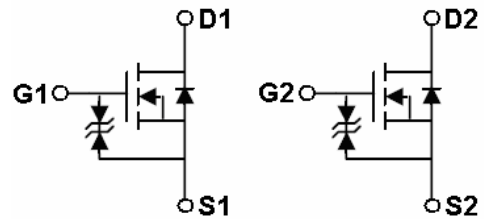
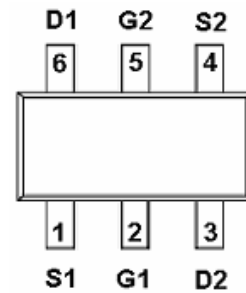
FEATURES

- ◆ 60V/0.50A , $R_{DS(ON)} = 2.0\Omega @ V_{GS} = 10V$
- ◆ 60V/0.20A , $R_{DS(ON)} = 4.0\Omega @ V_{GS} = 4.5V$
- ◆ Super high density cell design for extremely low $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ SOT-363 package design

APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, Display, Memories, Transistors, etc.
- High saturation current capability. Direct Logic-Level Interface: TTL/CMOS
- Battery Operated Systems
- Solid-State Relays

PIN CONFIGURATION (SOT-363 / SC-70-6L)



PART MARKING



Y : Year Code
W : Week Code



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PIN DESCRIPTION

Pin	Symbol	Description
1	S1	Source 1
2	G1	Gate 1
3	D2	Drain 2
4	S2	Source 2
5	G2	Gate 2
6	D1	Drain1

ORDERING INFORMATION

Part Number	Package	Part Marking
SPN7002TS36RGB	SOT-363	72TYW

※ Week Code : A ~ Z (1 ~ 26) ; a ~ z (27 ~ 52)

※ SPN7002TS36RGB : Tape Reel ; Pb – Free ; Halogen -Free

ABSOLUTE MAXIMUM RATINGS (TA=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V _{DSS}	60	V
Gate –Source Voltage - Continuous	V _{GSS}	±20	V
Continuous Drain Current(T _J =150°C)	I _D	0.64	A
Pulsed Drain Current (*)	I _{DM}	0.95	A
Power Dissipation	P _D	1.35	W
Operating Junction Temperature	T _J	-55 ~ 150	°C
Storage Temperature Range	T _{STG}	-55 ~ 150	°C
Thermal Resistance-Junction to Ambient	R _{θJA}	375	°C/W

(*) Pulse width limited by safe operating area



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ELECTRICAL CHARACTERISTICS (TA=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250Ua	60			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	1.0	1.7	2.5	
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±30	uA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V T _J =25°C			10	uA
		V _{DS} =48V, V _{GS} =0V T _J =70°C			100	
Drain-Source On-Resistance	R _{DSON}	V _{GS} =10V, I _D =0.50A			2.0	Ω
		V _{GS} = 4.5V, I _D =0.20A			4.0	
Forward Transconductance	G _{fs(1)}	V _{DS} = 10 V, I _D = 0.6 A		0.6		S
Diode Forward Voltage	V _{SD(1)}	V _{GS} = 0 V, I _S = 1.2A			1.2	V
Dynamic						
Total Gate Charge	Q _g	V _{DD} = 50 V, I _D = 0.6 A, V _{GS} = 4.5 V		1.0	1.6	nC
Gate-Source Charge	Q _{gs}			0.5		
Gate-Drain Charge	Q _{gd}			0.5		
Input Capacitance	C _{iss}	V _{DS} = 25 V, f = 1 MHz, V _{GS} = 0		32	50	pF
Output Capacitance	C _{oss}			8		
Reverse Transfer Capacitance	C _{rss}			6		
Turn-On Time	t _{d(on)}	V _{DD} = 30 V, I _D = 0.6 A R _G = 3.3Ω V _{GS} = 10.0 V R _D = 52Ω		12		ns
	t _r			10		
Turn-Off Time	t _{d(off)}			56		
	t _f			29		

(1) Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %.

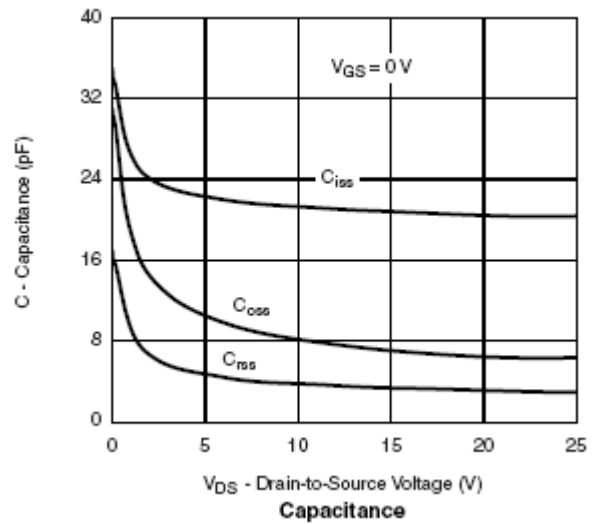
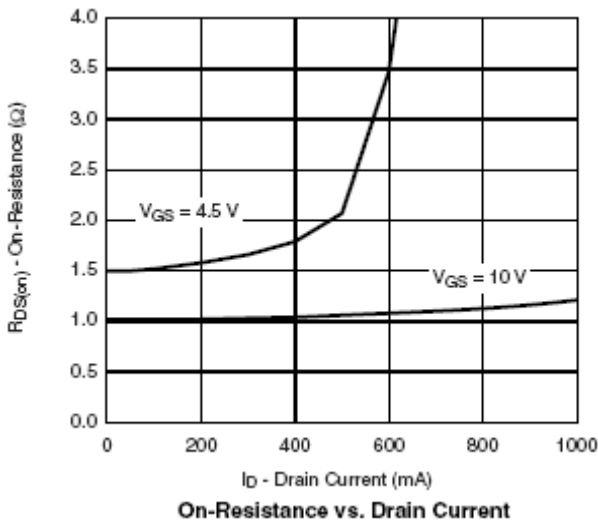
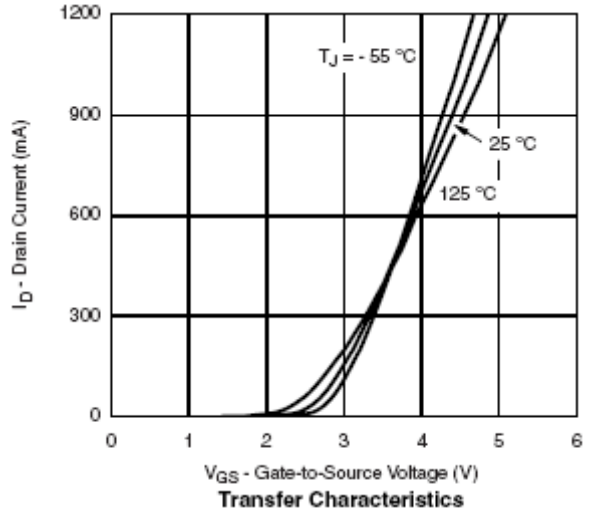
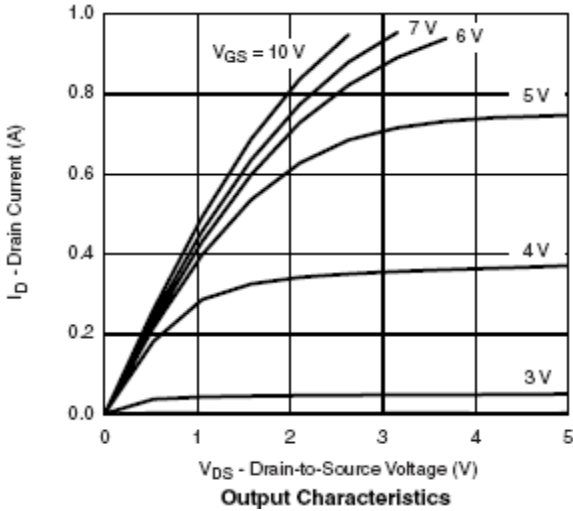
(2) Pulse width limited by safe operating area.



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TYPICAL CHARACTERISTICS

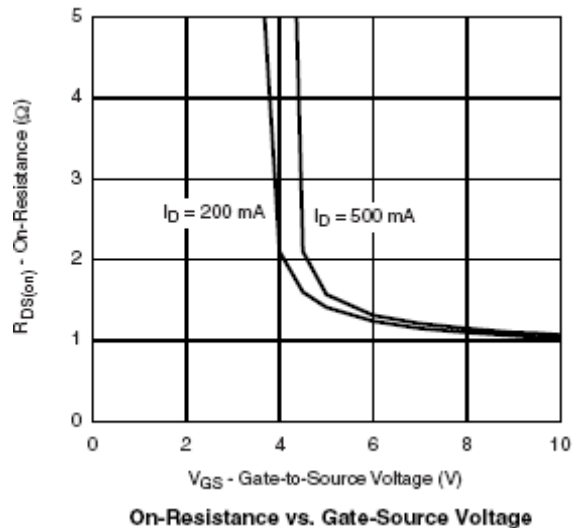
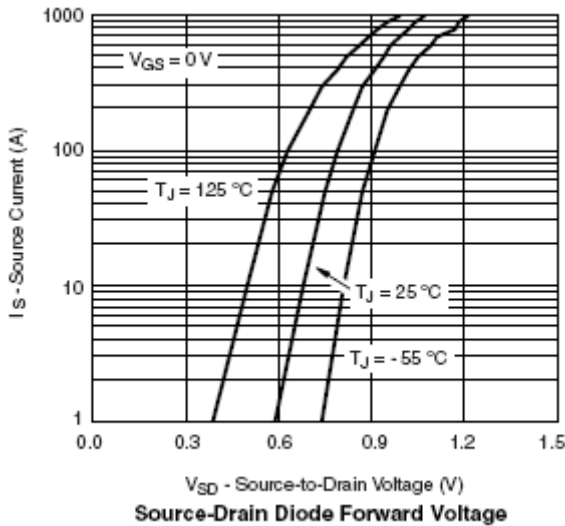
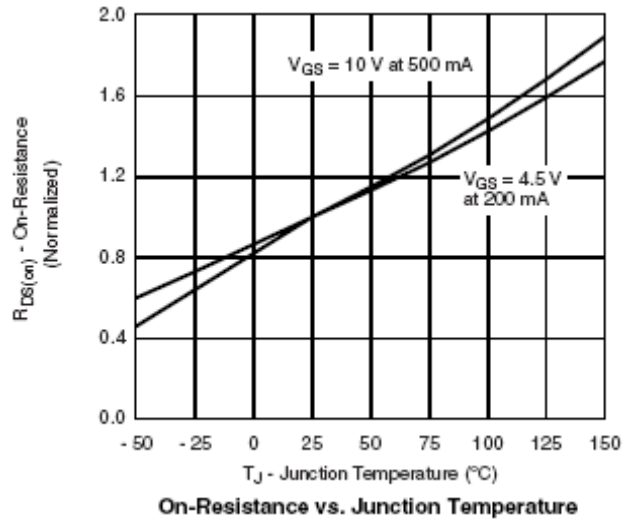
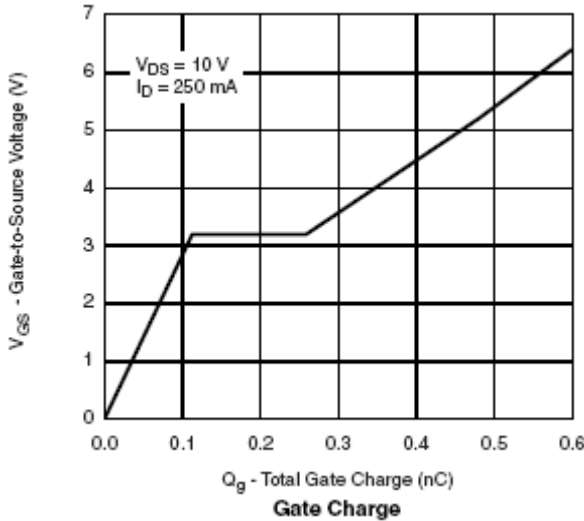




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TYPICAL CHARACTERISTICS

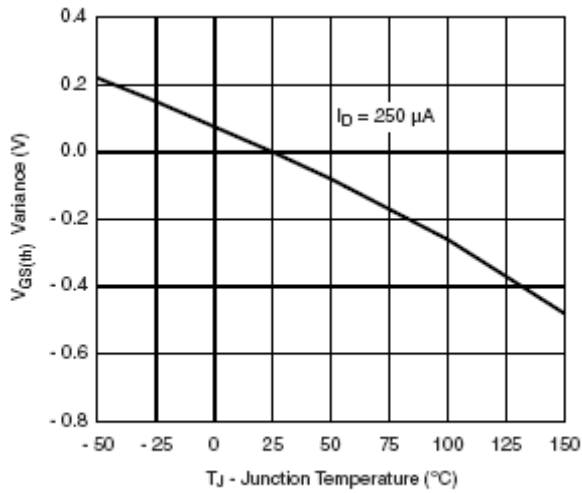




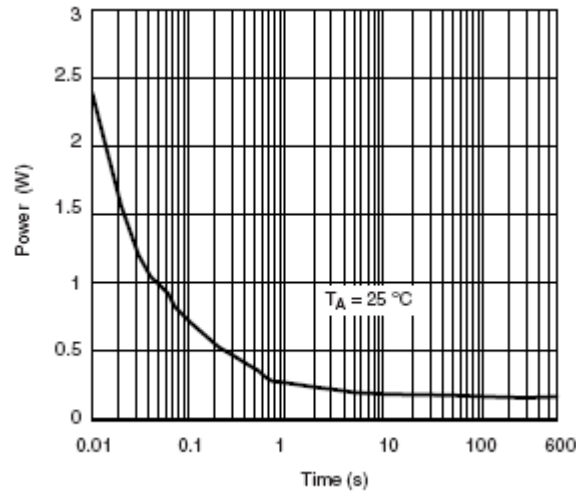
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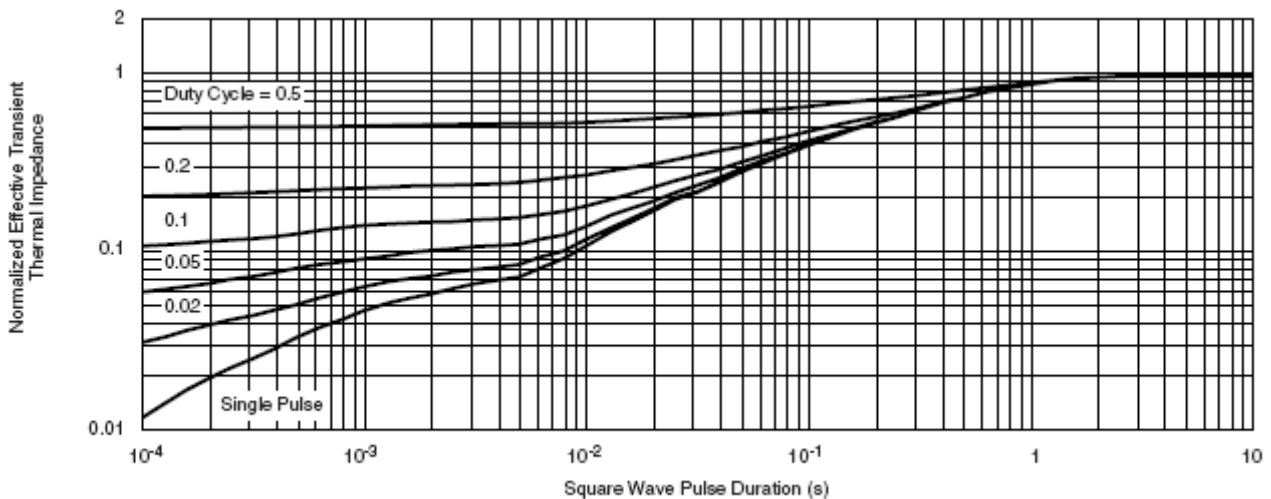
TYPICAL CHARACTERISTICS



Threshold Voltage Variance Over Temperature



Single Pulse Power, Junction-to-Ambient



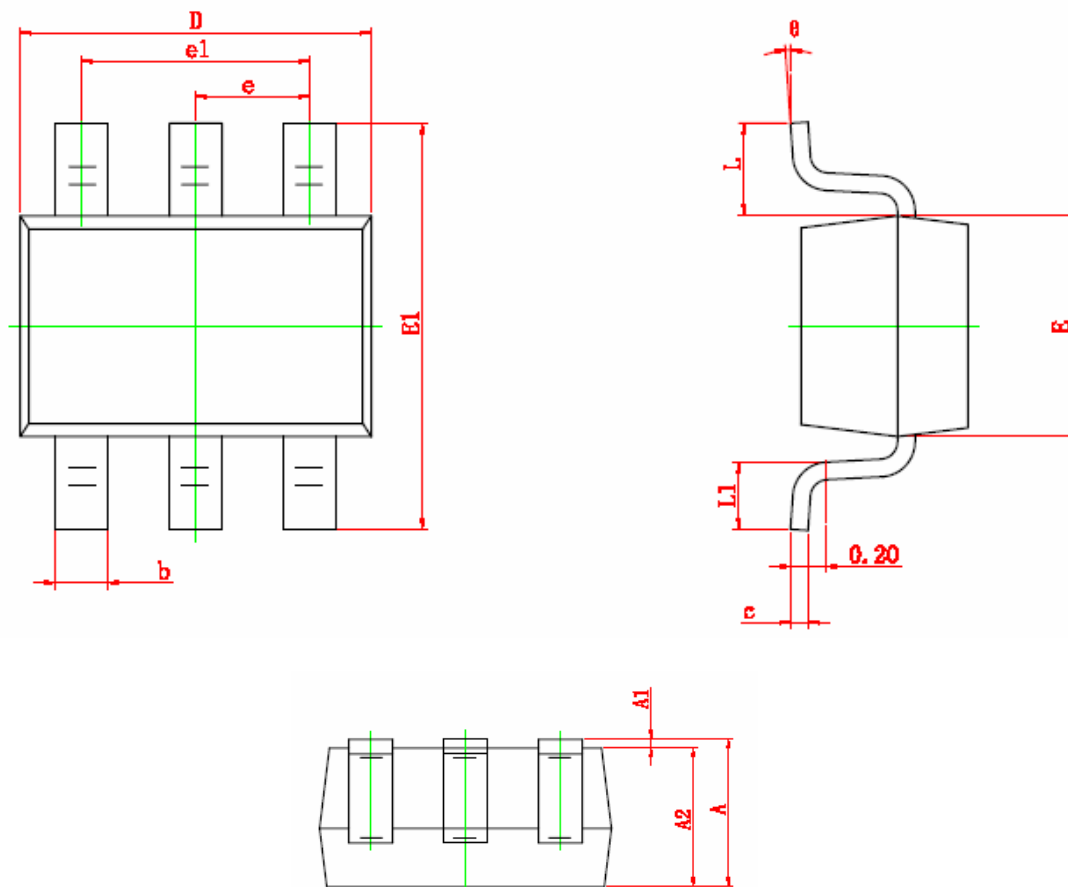
Normalized Thermal Transient Impedance, Junction-to-Foot



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SOT-363 PACKAGE OUTLINE



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°



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SYNC Power Corporation

7F-2, No.3-1, Park Street

NanKang District (NKSP), Taipei, Taiwan, 115, R.O.C

Phone: 886-2-2655-8178

Fax: 886-2-2655-8468

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